

Amendments to the Abstract:

Please replace the previously submitted Abstract with the following amended abstract:

--ABSTRACT OF THE DISCLOSURE

An integrated semiconductor memory is disclosed having selection transistors which can be formed at a respective ridge. The ridge can be arranged on an insulation layer. In the ridge the first source/drain region can be formed at ~~another~~ one lateral end of the ridge and the second source/drain region can be formed at another lateral end of the ridge. The longitudinal sides of the ridge and a top side of the ridge can be covered with a layer stack including a gate dielectric and a gate electrode. High write-read currents can be achieved in the on state of the selection transistors and leakage currents occurring in the off state can be ~~reduce~~ reduced. --